

**BJT DEVICE CONFIGURATION AND FABRICATION METHOD WITH
REDUCED EMITTER WIDTH**

ABSTRACT OF THE DISCLOSURE

A BJT device configuration includes an emitter finger and via arrangement which reduces emitter finger width, and is particularly suitable for use with compound
5 semiconductor-based devices. Each emitter finger includes a cross-shaped metal contact which provides an emitter contact; each contact comprises two perpendicular arms which intersect at a central area. A via through an inter-level dielectric layer provides access to the emitter
10 contact; the via is square-shaped, centered over the center point of the central area, and oriented at a 45° angle to the arms. This allows the via size to be equal to or greater than the minimum process dimension, while allowing the width of the emitter finger to be as narrow as possible
15 with the alignment tolerances still being met.